# XRD Line Broadening

*With effects on Selected Area Diffraction (SAD) Patterns in a TEM*



- **Example 3 Bragg's equation assumes:** 
	- $\Box$  Crystal is perfect and infinite
	- $\Box$  Incident beam is perfectly parallel and monochromatic
- Actual experimental conditions are different from these leading various kinds of deviations from Bragg's condition ⮚ Peaks are not 'δ' curves → Peaks are broadened *(in addition to other possible deviations)*
- There are also deviations from the assumptions involved in the generating powder patterns
	- ⮚ Crystals may not be randomly oriented *(textured sample) →* Peak intensities are altered w.r.t. to that expected
- **•** In a powder sample if the crystallite size  $\leq 0.5$  µm  $\Box$  there are insufficient number of planes to build up a sharp diffraction pattern ⇒ *peaks are broadened*

When considering **constructive and destructive interference** we considered the following points:

- In the example considered  $\theta$ ' was 'far away' (at a larger angular separation) from  $\theta$  ( $\theta_{\text{Bragg}}$ ) and it was easy to see the destructive interference
- In other words for incidence angle of  $\theta$ ' the phase difference of  $\pi$  is accrued just by traversing one 'd'.
- If the angle is just away from the Bragg angle  $(\theta_{\text{Bragg}})$ , then one will have to go deep into the crystal (many 'd') to find a plane (belonging to the same parallel set) which will scatter out of phase with this ray (phase difference of  $\pi$ ) and hence cause destructive interference
- If such a plane which scatters out of phase with a off Bragg angle ray is absent (due to finiteness of the crystal) then the ray will not be cancelled and diffraction would be observed just off Bragg angles too  $\rightarrow$  line broadening! *(i.e. the diffraction peak is not sharp like a δ-peak in the intensity versus angle plot)*
- This is one source of line broadening of line broadening. Other sources include: residual strain, instrumental effects, stacking faults etc.

# XRD Line Broadening



$$
B(FWHM) = B_i + B_c + B_s + B_{SF} + \dots
$$

The diffraction peak we see is a result of various broadening 'mechanisms' at work



Full Width at Half-Maximum (FWHM) is typically used as a measure of the peak 'width'

 $B(FWHM) = B_i + B_c + B_s + B_{SF} + ...$ 

Crystallite size  $\blacksquare$  Size > 10 µm  $\Box$  Spotty ring *(no. of grains in the irradiated portion insufficient to produce a ring)* **•** Size  $\in$  (10, 0.5)  $\mu$   $\Box$  Smooth continuous ring pattern Size  $\in (0.5, 0.1)$   $\mu \Box$  Rings are broadened Size  $\lt 0.1 \mu$   $\Box$  No ring pattern *(irradiated volume too small to produce a diffraction ring pattern & diffraction occurs only at low angles)* In a TEM Selected Area Diffraction (SAD) pattern, with decreasing crystallite size the following effects are observed on the pattern obtained





Few crystals in the selected region

## Effect of crystallite size on SAD patterns



*Schematics*

### Subtracting Instrumental Broadening

▪ Instrumental broadening has to be subtracted to get the broadening effects due to the sample

**1**

- Mix specimen with known coarse-grained (~ 10μm), well annealed *(strain free)* → does not give any broadening due to strain or crystallite size *(the broadening is due to instrument only ('Instrumental Broadening')).*  A brittle material which can be ground into powder form without leading to much stored strain is good for this purpose.
- $\Box$  If the pattern of the test sample (standard) is recorded separately then the experimental conditions should be identical *(it is preferable that one or more peaks of the standard lies close to the specimen's peaks)*

**2**

 $\Box$  Use the same material as the standard as the specimen to be X-rayed but with large grain size and well annealed

The peaks are fitted to various profiles…

$$
B(FWHM) = B_i + B_c + B_s + B_{SF} + ...
$$
  
\nFor a peak with a Lorentzian profile  
\n
$$
B - B_i \approx B_c + B_s = B_r
$$
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$$
L(x) = \frac{1}{\pi} \frac{1}{(x - x_0)^2 + (\frac{1}{2}\Gamma)^2}
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L(x) = \frac{1}{\pi} \frac{1}{(x - x_0)^2 + (\frac{1}{2}\Gamma)^2}
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\nFor a peak with a Gaussian profile  
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$$
L(x) = B_i - B_i
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L(x) = \frac{1}{\pi} \frac{1}{(x - x_0)^2 + (\frac{1}{2}\Gamma)^2}
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L(x) = \frac{1}{\pi} \frac{1
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#### Scherrer's formula *For Gaussian line profiles and cubic crystals*

The Scherrer's formula is used for the determination of grain size from broadened peaks. The formula is not expected to be valid for very small grain sizes  $(\leq 10 \text{ nm})$ 









 $14$ 

 $12$ 

 $\mathbf{t}$ 

100

80

Separating crystallite size broadening and strain broadening

$$
B_r = B_c + B_s
$$

$$
B_c = \frac{k \lambda}{L \cos(\theta)} \Bigg[.
$$

*Crystallite size broadening* 

$$
B_s = \eta \, Tan(\theta)
$$

*Strain broadening* 



$$
B_r \, Cos(\theta) = \frac{k\,\lambda}{L} + \eta \, Sin(\theta)
$$







*Annealed Al*



## *Cold-worked Al*



